

Article

3C-SiC Growth on Inverted Silicon Pyramids Patterned Substrate

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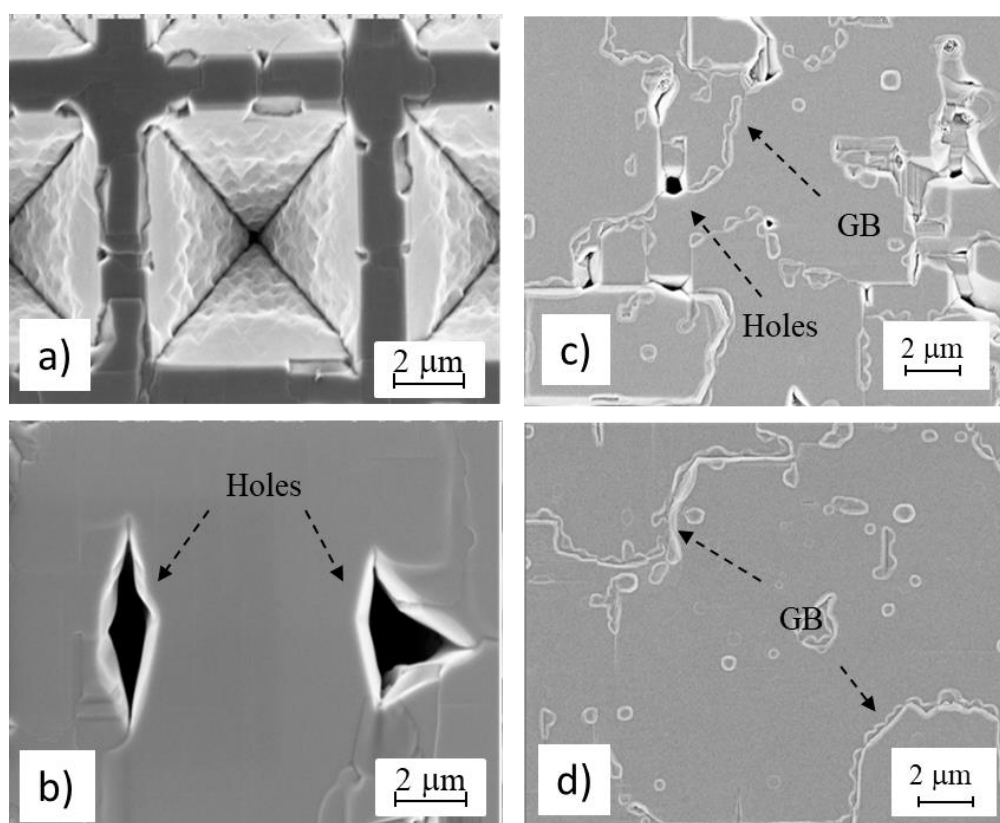


Figure S1. Plan view SEM image of SiC layer grown on ISP. (a) Pyramid size $5 \times 5 \mu\text{m}^2$ and layer thickness $1 \mu\text{m}$; (b) Pyramid size $5 \times 5 \mu\text{m}^2$ and layer thickness $10 \mu\text{m}$; (c) Pyramid size $3 \times 3 \mu\text{m}^2$ and layer thickness $6 \mu\text{m}$; (d) Pyramid size $1 \times 1 \mu\text{m}^2$ and layer thickness $6 \mu\text{m}$. Holes and grain boundaries (GB) are indicated.

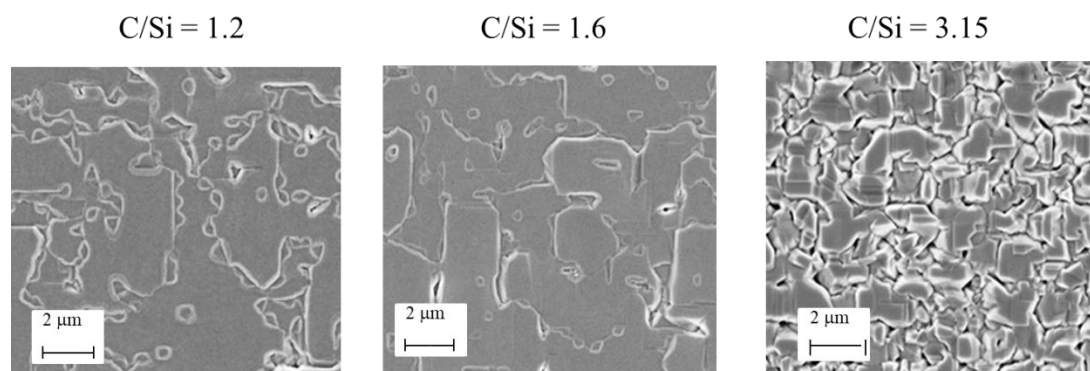


Figure S2. SEM plan view images of samples grown with a C/Si ratio between 1.2 and 3.15. Pyramid size was $1 \times 1 \mu\text{m}^2$.

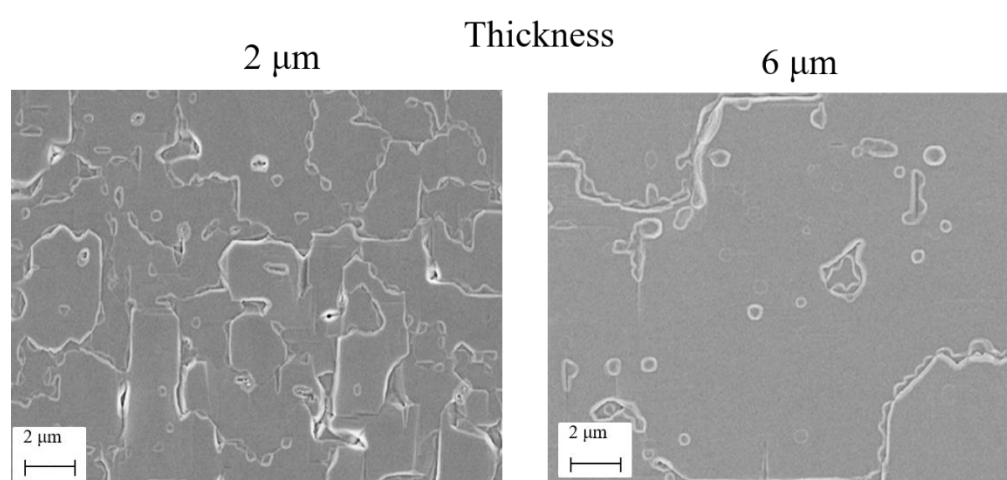


Figure S3. SEM plan view images of 2 μm and 6 μm thick 3C-SiC grown on $1 \times 1 \mu\text{m}^2$ pyramid.

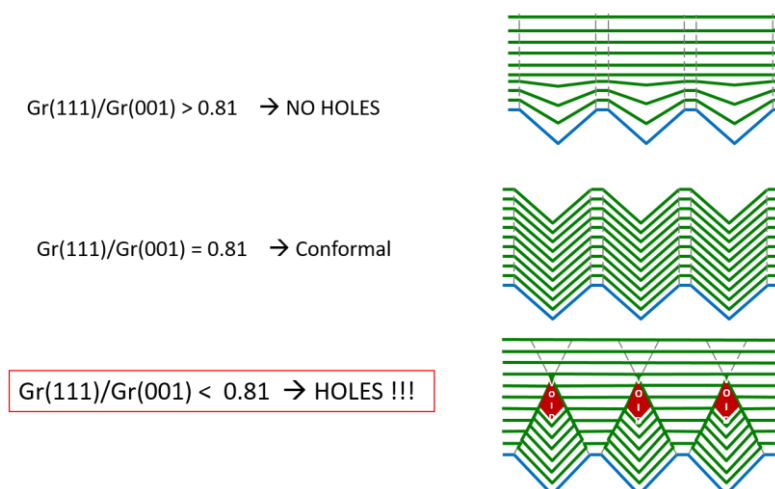


Figure S4. Ratio between (111) and (001) growth rates generating 3 different types of epilayer morphologies.